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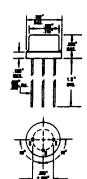
2N439 - 2N439A

NPN HIGH FREQUENCY COMPUTER TRANSISTORS

2N439 and 2N439A are NPN alloy-junction germanium transistors. Their basic NPN nature (high mobility electron flow) renders these transistors capable of very fast response under transient pulse operation. Their design is ideal for switching and flip-flop circuits. They are contained in a welded package equipped with flexible plated leads designed for connection by soldering, welding or socketing. This package has the mechanical dimensions of JETEC outline TO-9. The 2N439A has the base connected to the case internally to provide greater dissipation.

MECHANICAL DATA

JETEC outline TO-	9
JETEC base E3-5	1
Case material Meta	11
Maximum case length 0.250 inc	h
Maximum case diameter 0.360 inc	h
Minimum lead length 1.5 inche	s
Lead diameter 0.017 inc	h



ELECTRICAL DATA

RATINGS, ABSOLUTE MAXIMUM AT 25°C	2N439	<u>2N439A</u>
Collector to base voltage, V _{CB}	30	30 Vdc
Emitter to base voltage, VEB	25	25 Vdc
Collector to emitter voltage, VCE	20	20 Vdc
Total dissipation, P	100	150 mW
Derating per °C increase in ambient temperature	1.7	2.5 mW
Operating and storage temperature, T_j		-55 to +85°C

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL DATA

	Min.	Mode	Max.	<u>Units</u>		
STATIC AND LARGE SIGNAL PARAMETERS						
Collector cutoff current, I _{CBO} $V_{CB} = 25 \text{ V}$ Collector cutoff current, I _{CBO}		2	10	μAdc		
$V_{CB} = 6 \text{ V}, \text{ TA} = 75^{\circ}\text{C}$			150	μAdc		
Emitter cutoff current, IEBO VEB = 25 V		2	10	μAdc		
Emitter cutoff current, IEBO VEB = 6 V, TA = 75°C Collector-base breakdown voltage, BVCBO			150	μAdc		
$I_C = 100 \mu A$	30			Vdc		
Collector-emitter breakdown voltage, BVCEO $I_C = 300 \mu A$	20			Vdc		
Current gain, hre IC = 50 mA, VCE = 1.0 V	30	45				
Input voltage, VEB $I_C = 50 \text{ mA}$, $V_{CE} = 1.0 \text{ V}$.32	.7	Vdc		
Saturation resistance, Rs IC = 50 mA		3	5	ohms		
TYPICAL SWITCHING CHARACTERISTICS (Note	3)					
Rise time, t _r		.5		μs		
Fall time, t _f Storage time, t _s		.3 .7		ha ha		
LOW FREQUENCY, SMALL SIGNAL PARAMETERS (Note 1)						
Current gain, hie		35 27		ohms		
Input resistance, h _{ie} Input resistance, h _{ie}		1500		ohms		
HIGH FREQUENCY, SMALL SIGNAL PARAMETER	RS (Note	2)				
Cutoff frequency, $f_{\alpha b}$ Collector capacitance, C_c	5.0	9	20	mc μμ f		
Collector base time constant, rb'Cc		2300		μμs		
Extrinsic base resistance, rb'		220		ohms		

ENVIRONMENTAL

Hermetic seal - detergent and water at 60 psi for 1/2 hour.

Drop - 30 inches to maple block, 3 drops.

Shock - 500 g, 7 ms.

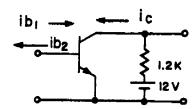
Vibration - 10 g, 100 - 1000 cps.

Lead bend - 3-180 degree bends on leads.

Note 1: VCB = 6.0 Vdc, IE = 1.0 mA, f = 270 cps

Note 2: $V_{CB} = 6.0 \text{ Vdc}$, $I_{E} = 1.0 \text{ mA}$, f = 455 kc

Note 3:



turn-on current $ib_1 = 1 mA$ turn-off current $ib_2 = 1 mA$ collector current $i_C = 10 mA$

